Oral presentation | 21 Joint Session K | 21.1 Joint Session K "Wide bandgap oxide semiconductor materials and devices"

[19p-224A-1~8] 21.1 Joint Session K "Wide bandgap oxide semiconductor materials and devices"

Keisuke Ide(Tokyo Tech.), Shizuo Fujita(京大)
Wed. Sep 19, 2018 1:00 PM - 3:15 PM  224A (224-1)
△: Presentation by Applicant for JSAP Young Scientists Presentation Award
▲: English Presentation
▼: Both of Above
No Mark: None of Above

1:00 PM - 1:30 PM
▲[19p-224A-1][JSAP Paper Award Speech] Delta-doped &beta;-gallium oxide field-effect transistor
Sriram Krishnamoorthy¹, Zhanbo Xia², Sanyam Bajaj², Mark Brenner², Siddharth Rajan² (1.Univ. of Utah, 2.Ohio State Univ.)
Keywords:JSAP Paper Award